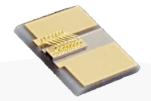
# High Power Laser Diode Chip on Carrier



#### Part Number: COC-107

High Power Chip on Carriers Multi-Mode Fabry-Perot Pulsed Wavelength at 1560nm



#### **Features**

- High Output Power
- High Dynamic Range
- High Efficiency
- Standard Chip on Carrier
- Cost Effective

### **Application**

- Laser Rangefinders
- Target Illumination



SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary, we will further optimize the design of our InP & GaSb laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.

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### Specification

#### COC-107



Optical	Symbol	Тур.	Units
Center Wavelength	λ <sub>c</sub>	1560	nm (±20)
Output Power (<10ns)*	Pout	30	watts (±10%)
Output Power (150ns)*	Pout	14	watts (±10%)
Emitter Width	W	95	μm
Spectral Width FWHM	Δλ	15	nm
Slope Efficiency	η	0.3	W/A
Fast Axis Div.	Θ⊥	30	deg FWHM
Slow Axis Div.	Θ <sub>  </sub>	10	deg FWHM
Electrical	Symbol		Units
Power Conversion Eff.	η	4	%
Operating Current (<10ns)	lop	100	А
Operating Current (<150ns)	lop	50	А
Threshold Current	Ітн	2	А
Operating Voltage	Vop	7	V
Duty Cycle	DC	0.1	%
Mechanical		Range	Units
Operating Temp.**		-40 to 60	°C
Storage Temp.		-40 to 80	°C

\*Specified values are rated at a constant heat sink temperature of 20°C.

\*\*High temperature operation will reduce performance and MTTF.

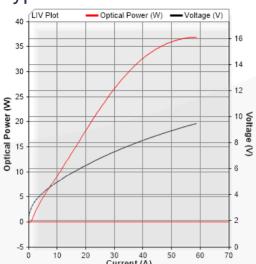
Unless otherwise indicated all values are nominal.

# High Power Laser Diode Chip on Carrier

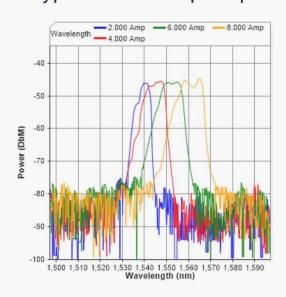


# SemiNex Laser Diodes COC-107 Graphs & Data

#### Typical COC L-I-V Characteristics



### Typical COC Output Spectrum



\*Tested with 150nsec pulse @ 0.1% Duty Cycle

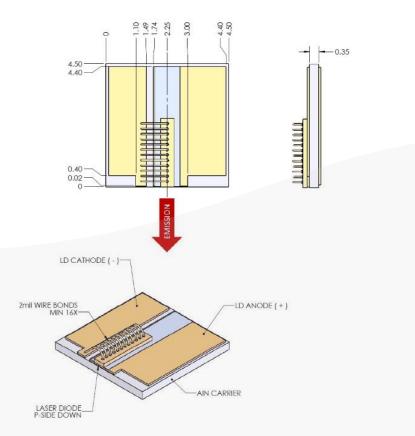


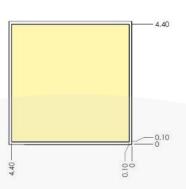
# High Power Laser Diode Chip on Carrier



#### **Mechanical Drawing**







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